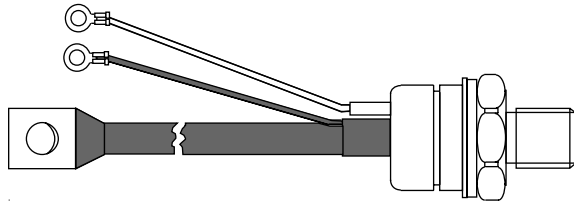


## Phase Control Thyristors (Stud Version), 200 A



TO-209AB (TO-93)

**FEATURES**

- Center amplifying gate
- International standard case TO-209AB (TO-93)
- Hermetic metal case with ceramic insulator (Also available with glass-metal seal up to 1200 V)
- Compression bonded encapsulation for heavy duty operations such as severe thermal cycling
- Lead (Pb)-free
- Designed and qualified for industrial level


**RoHS  
COMPLIANT**
**PRODUCT SUMMARY**

$I_{T(AV)}$	200 A
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**TYPICAL APPLICATIONS**

- DC motor controls
- Controlled DC power supplies
- AC controllers

**MAJOR RATINGS AND CHARACTERISTICS**

PARAMETER	TEST CONDITIONS	VALUES	UNITS
$I_{T(AV)}$		200	A
	$T_C$	85	°C
$I_{T(RMS)}$		314	A
$I_{TSM}$	50 Hz	5000	A
	60 Hz	5230	
$I^2t$	50 Hz	125	kA <sup>2</sup> s
	60 Hz	114	
$V_{DRM}/V_{RRM}$		400 to 2000	V
$t_q$	Typical	100	µs
$T_J$		- 40 to 125	°C

**ELECTRICAL SPECIFICATIONS**
**VOLTAGE RATINGS**

TYPE NUMBER	VOLTAGE CODE	$V_{DRM}/V_{RRM}$ , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	$V_{RSM}$ , MAXIMUM NON-REPETITIVE PEAK VOLTAGE V	$I_{DRM}/I_{RRM}$ MAXIMUM AT $T_J = T_J$ MAXIMUM mA
ST180S	04	400	500	30
	08	800	900	
	12	1200	1300	
	16	1600	1700	
	20	2000	2100	

ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS	
Maximum average on-state current at case temperature	$I_{T(AV)}$	180° conduction, half sine wave		200	A	
				85	°C	
Maximum RMS on-state current	$I_{T(RMS)}$	DC at 76 °C case temperature		314		
Maximum peak, one-cycle non-repetitive surge current	$I_{TSM}$	t = 10 ms	No voltage reapplied	5000	A	
		t = 8.3 ms		Sinusoidal half wave, initial $T_J = T_J$ maximum		5230
		t = 10 ms	100 % $V_{RRM}$ reapplied			4200
		t = 8.3 ms				4400
Maximum $I^2t$ for fusing	$I^2t$	t = 10 ms	No voltage reapplied		125	kA <sup>2</sup> s
		t = 8.3 ms		100 % $V_{RRM}$ reapplied	114	
		t = 10 ms	88			
		t = 8.3 ms	81			
Maximum $I^2\sqrt{t}$ for fusing	$I^2\sqrt{t}$	t = 0.1 to 10 ms, no voltage reapplied			1250	kA <sup>2</sup> /s
Low level value of threshold voltage	$V_{T(TO)1}$	$(16.7\% \times \pi \times I_{T(AV)} < I < \pi \times I_{T(AV)})$ , $T_J = T_J$ maximum		1.08	V	
High level value of threshold voltage	$V_{T(TO)2}$	$(I > \pi \times I_{T(AV)})$ , $T_J = T_J$ maximum		1.14		
Low level value of on-state slope resistance	$r_{t1}$	$(16.7\% \times \pi \times I_{T(AV)} < I < \pi \times I_{T(AV)})$ , $T_J = T_J$ maximum		1.18	mΩ	
High level value of on-state slope resistance	$r_{t2}$	$(I > \pi \times I_{T(AV)})$ , $T_J = T_J$ maximum		1.14		
Maximum on-state voltage	$V_{TM}$	$I_{pk} = 570$ A, $T_J = 125$ °C, $t_p = 10$ ms sine pulse		1.75	V	
Maximum holding current	$I_H$	$T_J = T_J$ maximum, anode supply 12 V resistive load		600	mA	
Maximum (typical) latching current	$I_L$			1000 (300)		

SWITCHING					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum non-repetitive rate of rise of turned-on current	$di/dt$	Gate drive 20 V, 20 Ω, $t_r \leq 1$ μs $T_J = T_J$ maximum, anode voltage $\leq 80\%$ $V_{DRM}$		1000	A/μs
Typical delay time	$t_d$	Gate current 1 A, $di_g/dt = 1$ A/μs $V_d = 0.67\%$ $V_{DRM}$ , $T_J = 25$ °C		1.0	μs
Typical turn-off time	$t_q$	$I_{TM} = 300$ A, $T_J = T_J$ maximum, $di/dt = 20$ A/μs, $V_R = 50$ V, $dV/dt = 20$ V/μs, gate 0 V 100 Ω, $t_p = 500$ μs		100	

BLOCKING					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum critical rate of rise of off-state voltage	$dV/dt$	$T_J = T_J$ maximum linear to 80 % rated $V_{DRM}$		500	V/μs
Maximum peak reverse and off-state leakage current	$I_{RRM}$ , $I_{DRM}$	$T_J = T_J$ maximum, rated $V_{DRM}/V_{RRM}$ applied		30	mA



<b>TRIGGERING</b>						
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES		UNITS
				TYP.	MAX.	
Maximum peak gate power	$P_{GM}$	$T_J = T_J$ maximum, $t_p \leq 5$ ms		10		W
Maximum average gate power	$P_{G(AV)}$	$T_J = T_J$ maximum, $f = 50$ Hz, $d\% = 50$		2.0		
Maximum peak positive gate current	$I_{GM}$	$T_J = T_J$ maximum, $t_p \leq 5$ ms		3.0		A
Maximum peak positive gate voltage	$+V_{GM}$	$T_J = T_J$ maximum, $t_p \leq 5$ ms		20		V
Maximum peak negative gate voltage	$-V_{GM}$			5.0		
DC gate current required to trigger	$I_{GT}$	$T_J = -40$ °C	Maximum required gate trigger/ current/voltage are the lowest value which will trigger all units 12 V anode to cathode applied	180	-	mA
		$T_J = 25$ °C		90	150	
		$T_J = 125$ °C		40	-	
DC gate voltage required to trigger	$V_{GT}$	$T_J = -40$ °C		2.9	-	V
		$T_J = 25$ °C		1.8	3.0	
		$T_J = 125$ °C		1.2	-	
DC gate current not to trigger	$I_{GD}$	$T_J = T_J$ maximum	Maximum gate current/voltage not to trigger is the maximum value which will not trigger any unit with rated $V_{DRM}$ anode to cathode applied	10		mA
DC gate voltage not to trigger	$V_{GD}$			0.25		V

<b>THERMAL AND MECHANICAL SPECIFICATIONS</b>				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum operating junction temperature range	$T_J$		- 40 to 125	°C
Maximum storage temperature range	$T_{Stg}$		- 40 to 150	
Maximum thermal resistance, junction to case	$R_{thJC}$	DC operation	0.105	K/W
Maximum thermal resistance, case to heatsink	$R_{thC-hs}$	Mounting surface, smooth, flat and greased	0.04	
Mounting torque, $\pm 10$ %		Non-lubricated threads	31 (275)	N · m (lbf · in)
		Lubricated threads	24.5 (210)	
Approximate weight			280	g
Case style		See dimensions - link at the end of datasheet	TO-209AB (TO-93)	

<b><math>\Delta R_{thJC}</math> CONDUCTION</b>				
CONDUCTION ANGLE	SINUSOIDAL CONDUCTION	RECTANGULAR CONDUCTION	TEST CONDITIONS	UNITS
180°	0.015	0.012	$T_J = T_J$ maximum	K/W
120°	0.019	0.020		
90°	0.025	0.027		
60°	0.036	0.037		
30°	0.060	0.060		

**Note**

- The table above shows the increment of thermal resistance  $R_{thJC}$  when devices operate at different conduction angles than DC

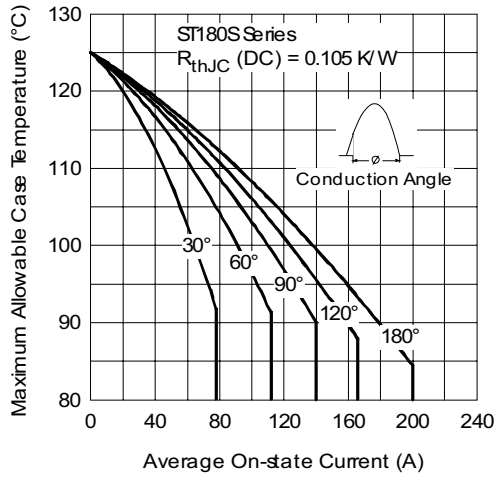


Fig. 1 - Current Ratings Characteristics

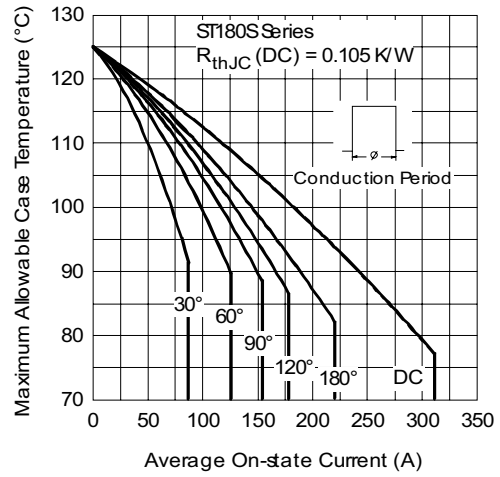


Fig. 2 - Current Ratings Characteristics

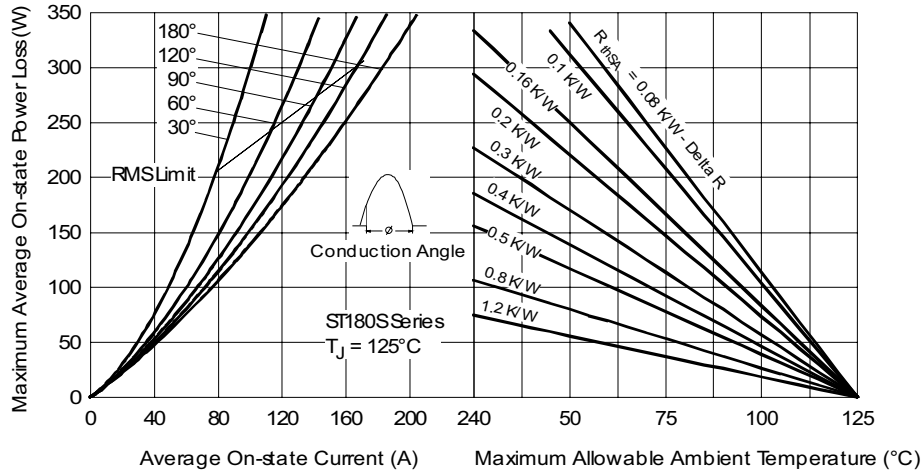


Fig. 3 - On-State Power Loss Characteristics

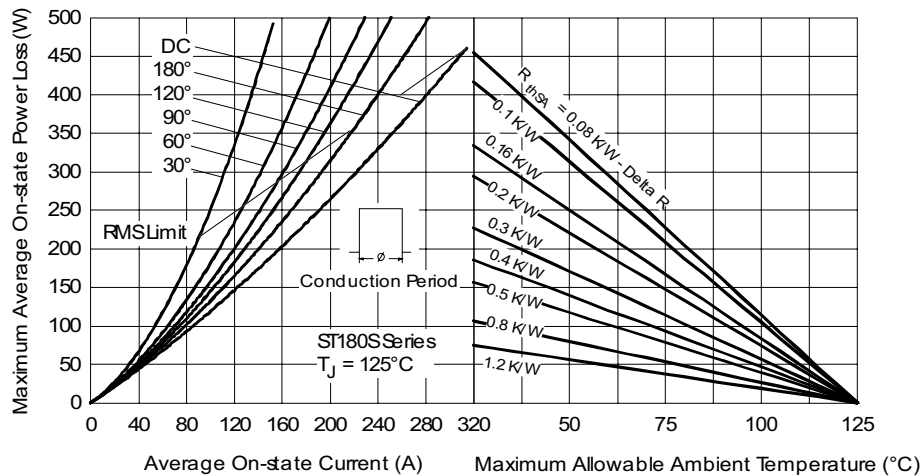


Fig. 4 - On-State Power Loss Characteristics

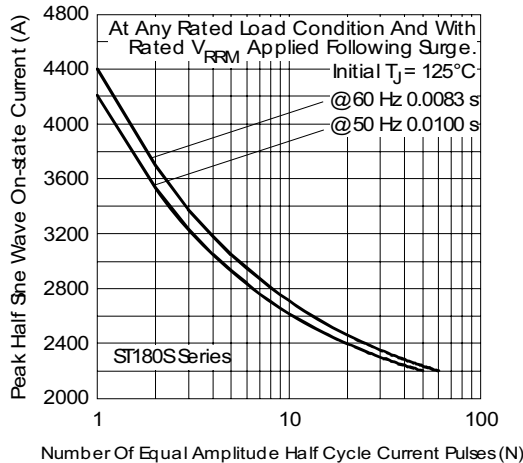


Fig. 5 - Maximum Non-Repetitive Surge Current

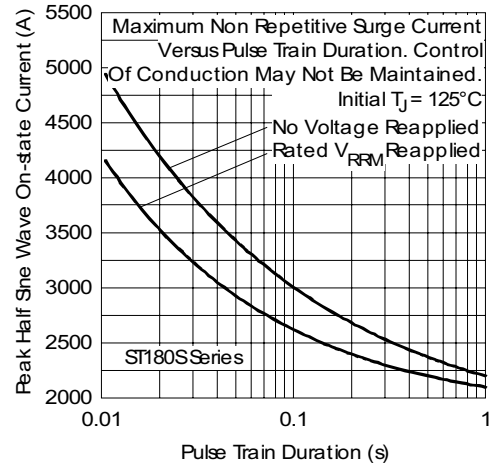


Fig. 6 - Maximum Non-Repetitive Surge Current

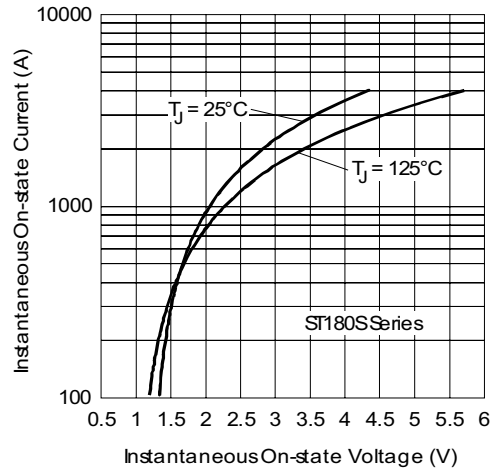


Fig. 7 - On-State Voltage Drop Characteristics

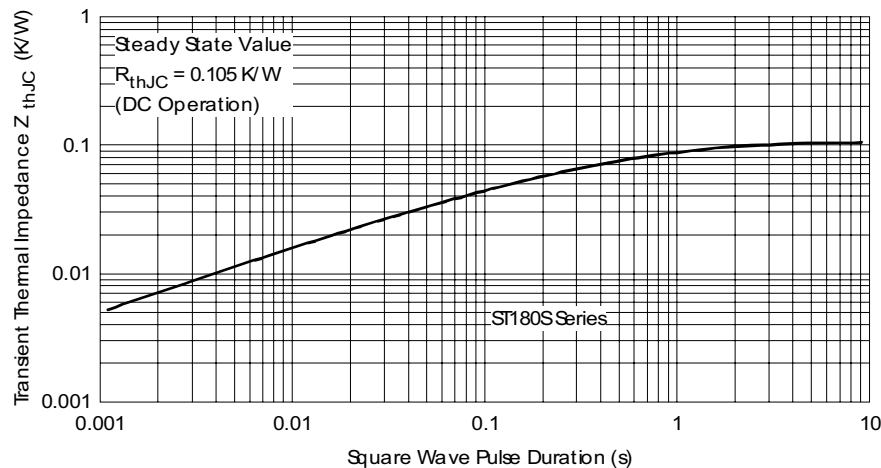


Fig. 8 - Thermal Impedance  $Z_{thJC}$  Characteristics

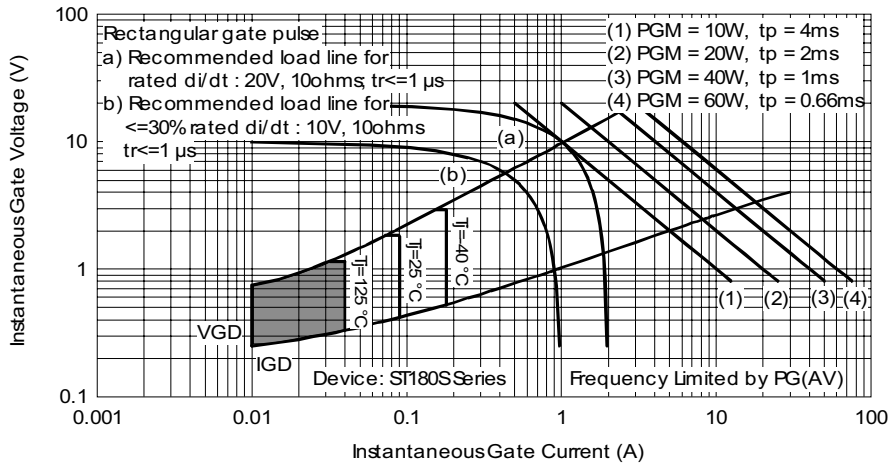


Fig. 9 - Gate Characteristics

## ORDERING INFORMATION TABLE

Device code	ST	18	0	S	20	P	0	-	PbF
	①	②	③	④	⑤	⑥	⑦	⑧	⑨

- 1** - Thyristor
- 2** - Essential part number
- 3** - 0 = Converter grade
- 4** - S = Compression bonding stud
- 5** - Voltage code x 100 =  $V_{RRM}$  (see Voltage Ratings table)
- 6** - P = Stud base 3/4"-16UNF2A threads
- 7** - 0 = Eyelet terminals (gate and auxiliary cathode leads)  
1 = Fast-on terminals (gate and auxiliary cathode leads)
- 8** - V = Glass-metal seal (only up to 1200 V)  
None = Ceramic housing (over 1200 V)
- 9** - Lead (Pb)-free

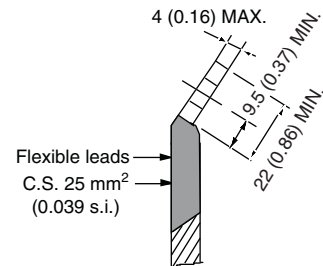
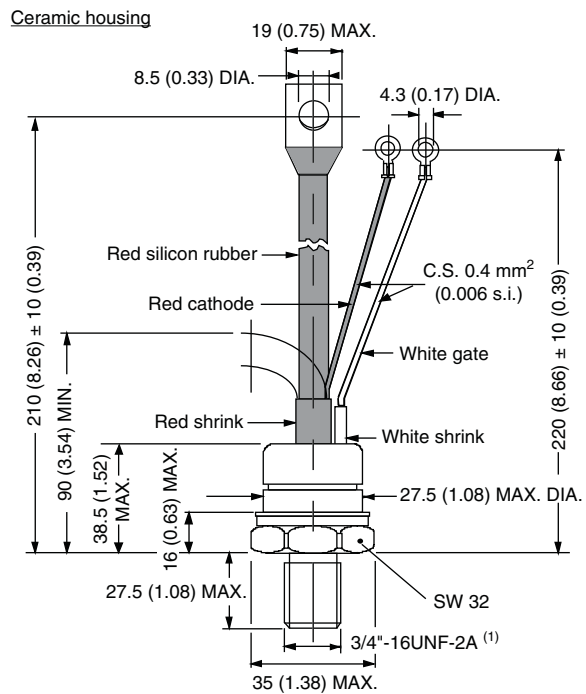
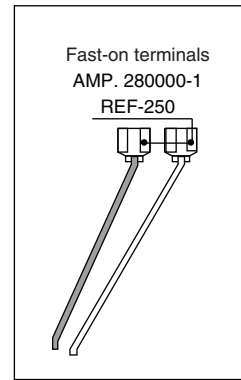
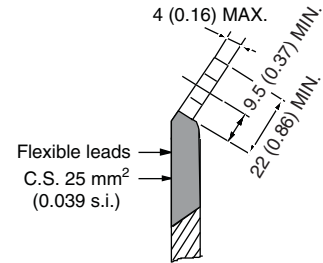
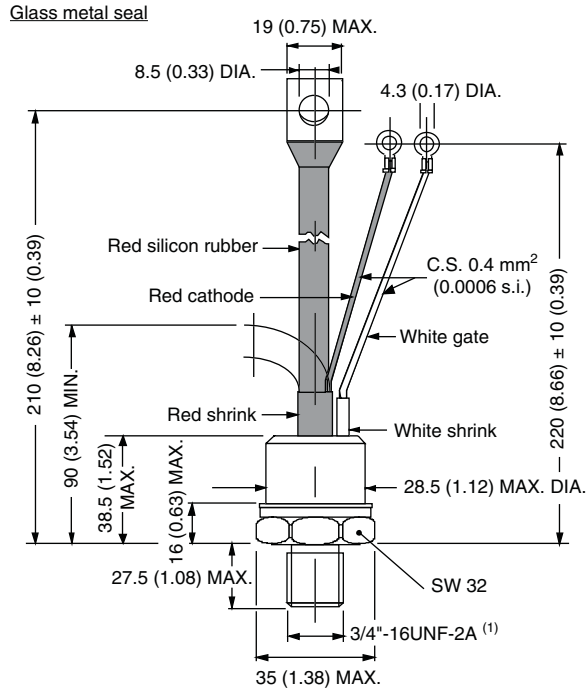
Note: For metric device M16 x 1.5 contact factory

### LINKS TO RELATED DOCUMENTS

Dimensions	<a href="http://www.vishay.com/doc?95082">http://www.vishay.com/doc?95082</a>
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## TO-209AB (TO-93)

**DIMENSIONS** in millimeters (inches)



**Note**

(1) For metric device: M16 x 1.5 - length 21 (0.83) maximum



## Disclaimer

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